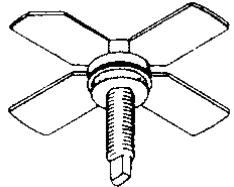
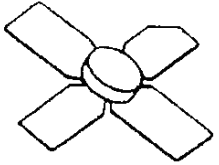




# MS652/MS652S

5.0 Watts, 12.5 Volts, Class C  
UHF Applications

<b>GENERAL DESCRIPTION</b> The <b>MS652/MS652S</b> is a common emitter and 12.5V Class C epitaxial silicon NPN planar transistor designed primarily for UHF communications. It withstands severe mismatch under normal operating conditions.		 <b>.280 4L STUD(M122), Epoxy sealed MS652</b>   <b>.280 4LSL (M123), Epoxy sealed MS652S</b>													
<b>ABSOLUTE MAXIMUM RATINGS</b> <table border="0"> <tr> <td>Maximum Power Dissipation @ 25°C</td> <td>25 Watts</td> </tr> <tr> <td>BV<sub>CBO</sub> Collector to Base Voltage</td> <td>36 Volts</td> </tr> <tr> <td>BV<sub>CEO</sub> Collector to Emitter Voltage</td> <td>16 Volts</td> </tr> <tr> <td>BV<sub>EBO</sub> Emitter to Base Voltage</td> <td>4.0 Volts</td> </tr> <tr> <td>I<sub>C</sub> Collector Current</td> <td>2.0 Amps</td> </tr> <tr> <td>Storage Temperature</td> <td>-65 to +150 °C</td> </tr> <tr> <td>Operating Junction Temperature</td> <td>+200 °C</td> </tr> </table>			Maximum Power Dissipation @ 25°C	25 Watts	BV <sub>CBO</sub> Collector to Base Voltage	36 Volts	BV <sub>CEO</sub> Collector to Emitter Voltage	16 Volts	BV <sub>EBO</sub> Emitter to Base Voltage	4.0 Volts	I <sub>C</sub> Collector Current	2.0 Amps	Storage Temperature	-65 to +150 °C	Operating Junction Temperature
Maximum Power Dissipation @ 25°C	25 Watts														
BV <sub>CBO</sub> Collector to Base Voltage	36 Volts														
BV <sub>CEO</sub> Collector to Emitter Voltage	16 Volts														
BV <sub>EBO</sub> Emitter to Base Voltage	4.0 Volts														
I <sub>C</sub> Collector Current	2.0 Amps														
Storage Temperature	-65 to +150 °C														
Operating Junction Temperature	+200 °C														

## FUNCTIONAL CHARACTERISTICS @ 25°C

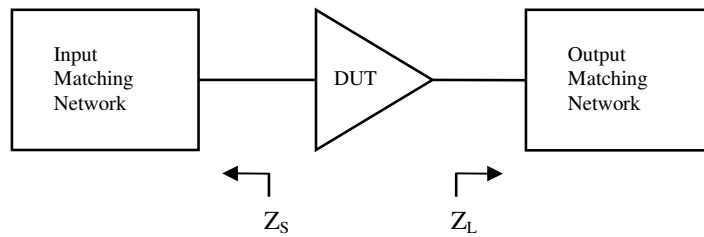
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>OUT</sub>	Power Out	F = 512 MHz V <sub>CE</sub> = 12.5V	5.0	-	-	W
P <sub>IN</sub>	Power Input		-	-	0.5	W
G <sub>p</sub>	Power Gain		10.0	-	-	dB
η	Efficiency	P <sub>OUT</sub> = 5W	60	-	-	%

## ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
BV <sub>CES</sub>	Collector to Emitter Breakdown	I <sub>C</sub> = 25 mA, V <sub>BE</sub> = 0	36	-	-	V
BV <sub>CEO</sub>	Collector to Emitter Breakdown	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0	16	-	-	V
BV <sub>CBO</sub>	Collector to Base Breakdown	I <sub>C</sub> = 25 mA, I <sub>E</sub> = 0	36	-	-	V
BV <sub>EBO</sub>	Emitter to Base Breakdown	I <sub>E</sub> = 5 mA, I <sub>C</sub> = 0	4.0	-	-	V
I <sub>CES</sub>	Collector to Emitter Leakage	V <sub>CE</sub> = 15 V, V <sub>BE</sub> = 0	-	-	1.0	mA
h <sub>FE</sub>	DC – Current Gain	I <sub>C</sub> = 200 mA, V <sub>CE</sub> = 5 V	10	-	150	-
C <sub>OB</sub>	Output Capacitance	F = 1MHz, V <sub>CB</sub> = 15V	-	-	15	pF
θ <sub>jc</sub> <sup>1</sup>	Junction-Case Thermal Resistance		-	-	7	°C/W

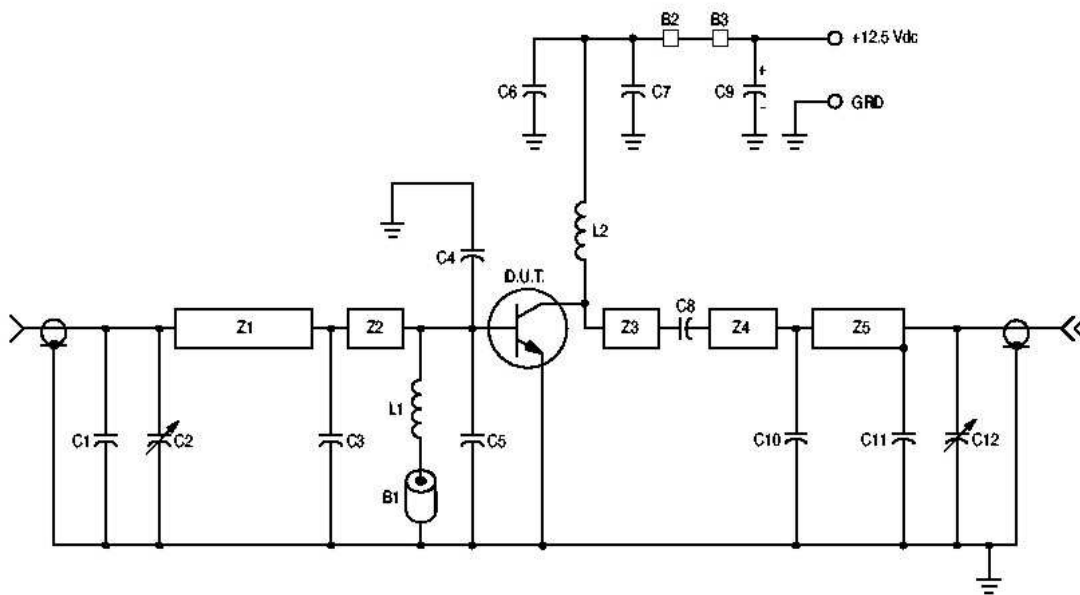
NOTES: 1. At rated output power with MSC fixture.  
Rev. A: May, 2010

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**Typical Impedance Values**

Frequency (MHz)	$Z_S$ ( $\Omega$ )	$Z_L$ ( $\Omega$ )
<b>400</b>	<b><math>1.2 - j0.6</math></b>	<b><math>6.5 + j6.5</math></b>
<b>440</b>	<b><math>1.2 - j0.9</math></b>	<b><math>7.2 + j6.0</math></b>
<b>470</b>	<b><math>1.2 - j1.2</math></b>	<b><math>7.7 + j5.3</math></b>
<b>512</b>	<b><math>1.2 - j1.5</math></b>	<b><math>8.3 + j4.5</math></b>

\*  $V_{CC} = 12.5V$ ,  $P_{OUT} = 5W$

**440 - 512 MHz Broadband Test Circuit**


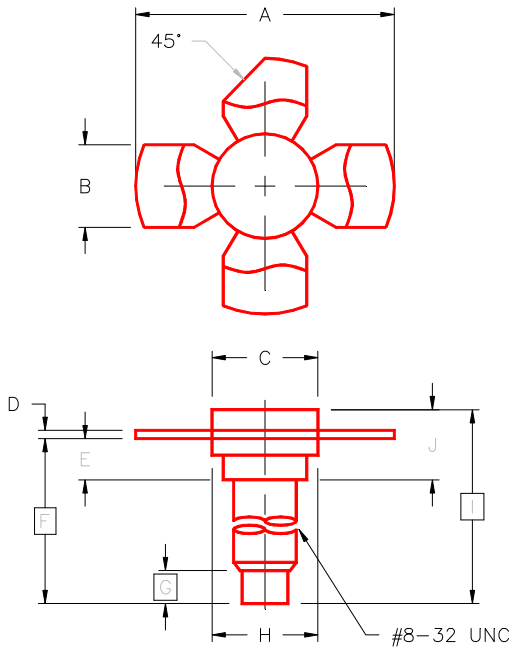
B1, B2, B3 — Ferrite Bead  
 C1 — 7.0 pF Unelco Mica  
 C2 — 1.0–6.0 pF Johanson Variable 5201  
 C3 — 15 pF Unelco Mica  
 C4 — 43 pF Mini–Underwood Mica  
 C5 — 56 pF Mini–Underwood Mica  
 C6 — 1000 pF Unelco Mica  
 C7 — 0.1  $\mu$ F Ceramic

C8 — 68 pF Mini–Underwood Mica  
 C9 — 1.0  $\mu$ F Electrolytic 25 V  
 C10, C11 — 5.0 pF Unelco Mica  
 C12 — 1.0–10 pF Johanson Variable 5501  
 L1, L2 — 6 Turns, 20 AWG Wire 0.125" ID  
 Z1, Z2 — 25 Ohm  $\mu$ Stripline  
 Z3, Z4, Z5 — 50 Ohm  $\mu$ Stripline  
 Board — 0.032" Glass–Teflon



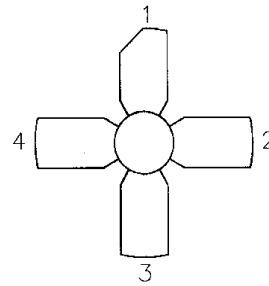
# MS652/MS652S

## PACKAGE STYLE M122



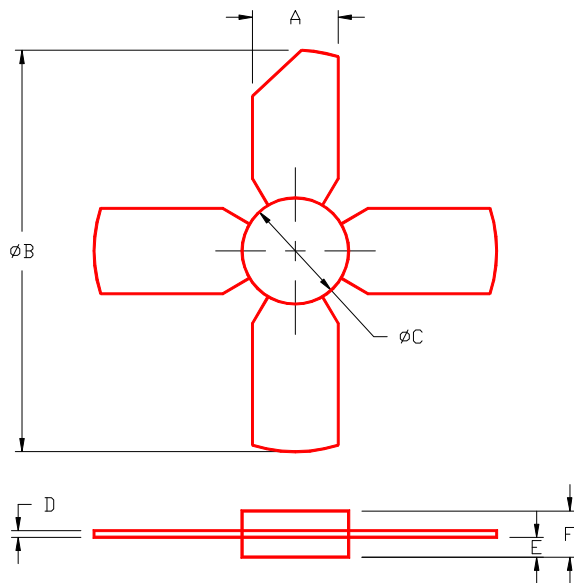
	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	1.010/25,65	1.055/26,80	I	.640/16,26	
B	.220/5,59	.230/5,84	J	.175/4,45	.217/5,51
C	.270/6,86	.285/7,24			
D	.003/0,08	.007/0,18			
E	.117/2,97	.137/3,48			
F	.572/14,53				
G	.130/3,30				
H	.275/6,99	.285/7,24			

### PIN CONNECTION



- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter

## PACKAGE STYLE M123



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.220/5,59	.230/5,84			
B	-----	1.055/26,8			
C	.275/6,99	.285/7,24			
D	.004/0,10	.006/0,15			
E	.050/1,27	.060/1,52			
F	.118/3,00	.130/3,30			

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